COMPLIANT



## Vishay Semiconductors

# **HEXFRED® Ultrafast Soft Recovery Diode, 220 A**



PRIMARY CHARACTERISTICS					
V <sub>R</sub>	1200 V				
V <sub>F</sub> (typical)	2.68 V				
t <sub>rr</sub> (typical)	58 ns				
I <sub>F(AV)</sub> per module at T <sub>C</sub>	220 A at 38 °C				
Package	SOT-227				

### **FEATURES**

- · Fast recovery time characteristic
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- · Designed and qualified for industrial level
- UL approved file E78996



### **DESCRIPTION / APPLICATIONS**

The dual diode series configuration (VS-HFA220FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V <sub>R</sub>		1200	V	
Continuous forward current	l <sub>F</sub>	T <sub>C</sub> = 68 °C	110	۸	
Single pulse forward current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	700	А	
Martin and advantage of the control of	Ь	T <sub>C</sub> = 25 °C	500	W	
Maximum power dissipation per leg P <sub>D</sub>		T <sub>C</sub> = 100 °C	400	VV	
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 minute	2500	V	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA	1200	-	-	
Forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 100 A	-	2.68	3.60	V
		I <sub>F</sub> = 200 A	-	3.41	4.70	
		I <sub>F</sub> = 100 A, T <sub>J</sub> = 150 °C	-	2.62	2.89	
		I <sub>F</sub> = 200 A, T <sub>J</sub> = 150 °C	-	3.59	3.89	
		$V_R = V_R$ rated	-	10	75	μA
Reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	2	-	A
		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{ rated}$	-	6	15	mA



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A$ ; $dI_F/dt$	$=$ - 200 A/ $\mu$ s; $V_R$ $=$ 30 V	1	58	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	157	-	ns
		T <sub>J</sub> = 125 °C		-	255	-	]
Dook room ourrent		T <sub>J</sub> = 25 °C	$I_F = 50 \text{ A}$	-	15	-	Α
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_B = 200 \text{ V}$	-	22.5	-	A
Poverse receivent charge	0	T <sub>J</sub> = 25 °C	"	-	1150	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2850	-	IIC
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 1200 V		-	53	-	pF

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	В		-	-	0.25	
Junction to case, both legs conducting	- R <sub>thJC</sub>		-	-	0.125	°C/W
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.10	-	1
Weight			-	30	-	g
Manustinas tanana		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style			SOT-227			

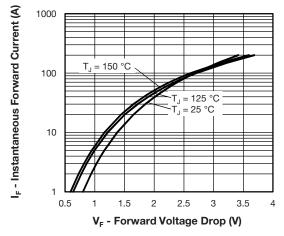


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

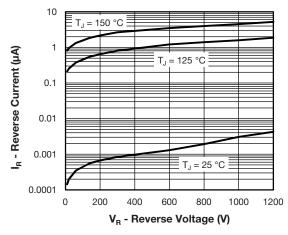


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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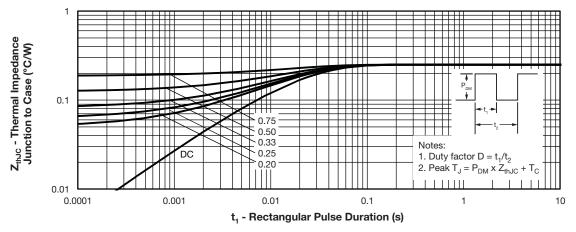


Fig. 3 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

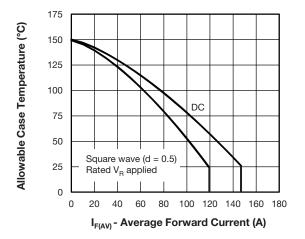


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

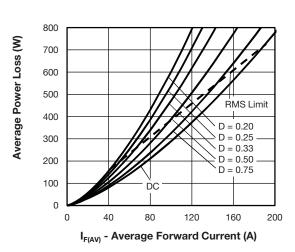


Fig. 5 - Forward Power Losses Characteristics (Per Leg)

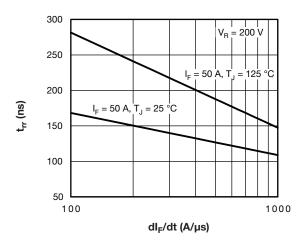


Fig. 6 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

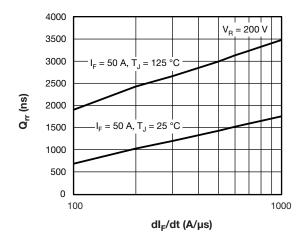


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt



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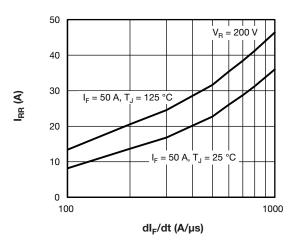


Fig. 8 - Typical Peak Recovery Current vs. dl<sub>F</sub>/dt

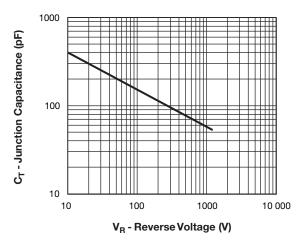


Fig. 9 - Typical Junction Capacitance vs. Reverse Voltage

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

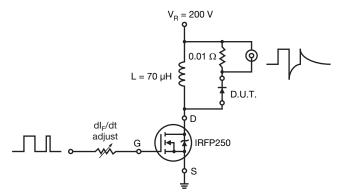
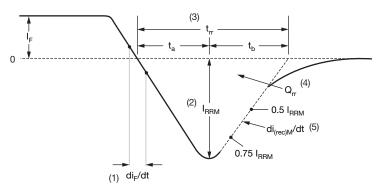


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

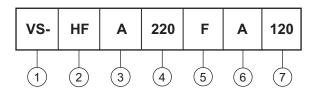
Fig. 11 - Reverse Recovery Waveform and Definitions



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## **ORDERING INFORMATION TABLE**

Device code



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- Process designator (A = electron irradiated)
- 4 Average current (220 = 220 A)
- 5 Circuit configuration (two separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (120 = 1200 V)

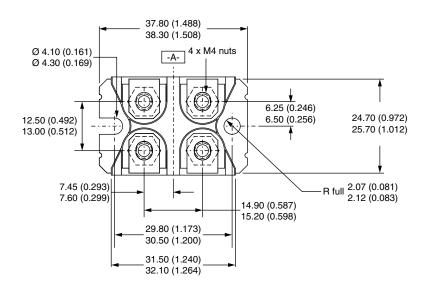
CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
Two separate diodes, parallel pin-out	F	Lead Assignment  4			

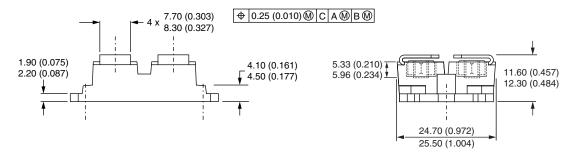
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95423</u>					
Packaging information	www.vishay.com/doc?95425				

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## SOT-227 Generation 2

## **DIMENSIONS** in millimeters (inches)





### Note

· Controlling dimension: millimeter



## **Legal Disclaimer Notice**

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